

# 0.65W, 5kV<sub>RMS</sub> Complete Isolated DC-DC Converter

#### 1 Features

#### Complete Switch Mode Power Supply

- High integration with internal transformer
- Soft-start reduces input inrush current and output overshoot
- Overload and short-circuit protection
- Thermal shutdown
- 4.5 V to 5.5 V Input Voltage Range
- Selectable Output voltages
- 3.3V, 3.7V, 5V and 5.4V output options
- Delivers up to 650mW(5V/130mA) Output Power
- Robust Galvanic Isolation Barrier
- High lifetime: > 40 years
- Up to 5000 V<sub>RMS</sub> isolation rating
- ±150 kV/μs typical CMTI
- Wide Operating Temperature Range: -40°C to 125°C
- Low Profile SOIC16-WB (10.30mm × 7.50) Package
- Safety-Related Certifications (Pending)
- 5kV<sub>RMS</sub> isolation for 1 minute per UL 1577
- 7071V<sub>PK</sub> V<sub>IOTM</sub> and 849V<sub>PK</sub> V<sub>IORM</sub> reinforced isolation per DIN V VDE V 0884-11:2017-01
- IEC 60950 \ IEC 60601 and EN 61010 certifications per CQC, TUV and CSA

#### 2 Applications

- Instruments and Apparatuses
- Industrial automation
- Motor Control
- Medical Equipment
- Industrial Sensors
- Telecom Equipment

# 3 General Description

The CA-IS3105 is a complete isolated DC-DC converter with up to  $5kV_{RMS}$  isolation rating. This device integrates most of the components needed for an isolated power supply — switching controller, power switches, transformer, soft-start, protection circuit etc. — into a single, compact SOIC package. The result is an efficient and compact fully integrated solution that is easy to comply with EMI

requirements and makes power-supply design as easy as possible. Operating over an input voltage range of 4.5V to 5.5V, the CA-IS3105 provides a fixed output voltage of 3.3V, 3.7V, 5V or 5.4V set by pin SEL. Only output, input bypass capacitors, and a pull-up resistor (3.7V or 5.4V output) are needed to finish the design.

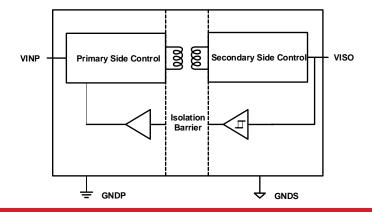
The CA-IS3105 features a unique control scheme, which can quickly respond to load transient and accurately regulate the output voltage. The device is capable of delivering a load up to 650mW output power and offering soft-start, current limit, short-circuit and thermal shutdown protection features to better enhance the reliability of the system. The CA-IS3105 includes an enable input pin (EN). Connect the EN pin to the VINP input voltage pin or force this pin high to turn on the DC-DC converter. Force this pin low to disable the device and enter shutdown mode. In shutdown mode, the device stops switching operation with microampere standby supply current.

The CA-IS3105 is available in wide-body SOIC16 package and operates over -40°C to +125°C temperature range.

#### **Device Information**

Part number	Package	Package size (NOM)
CA-IS3105W	SOIC16-WB(W)	10.30 mm × 7.50 mm

#### **Simplified Block Diagram**





# 4 Ordering Information

**Table 4-1. Ordering Information** 

Part #	Input Voltage Output Voltage Output Power		Package	
CA-IS3105W	4.5V to 5.5V	3.3V, 3.7V, 5V, 5.4V	650mW	SOIC16-WB(W)



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# 5 Revision history

Revision Number	Description	Page Changed	Revision Date
Version 1.00	N/A	N/A	2022-03-22



#### **Pin Configuration and Description** 6

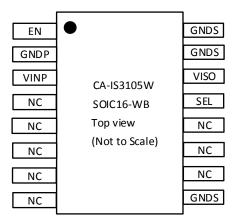


Figure 6-1 CA-IS3105W Top View

Table. 6-1 CA-IS3105W Pin Description

Pin name	Pin number	Туре	Description
EN	1	Input	Enable Input Pin, active-high. Force this pin high to enable the device. Force this pin low to disable the device and enter shutdown mode.
GNDP	2	GND	Primary side local ground.
VINP	3	Power	Primary side supply input. Bypass VINP to GNDP with both $0.1\mu F$ and $10\mu F$ capacitors as close to the device as possible.
NC <sup>1</sup>	4, 5, 6, 7, 8	-	No internal connection. These pins belong to primary side voltage domain. Connect them to GNDP externally.
GNDS	9, 15, 16	GND	Secondary side ground return connection for V <sub>ISO</sub> .
NC <sup>1</sup>	10, 11, 12	-	No internal connection. These pins belong to isolated voltage domain. Connect them to GNDS externally.
SEL	13	Input	Output voltage $V_{ISO}$ select pin: $V_{ISO} = 5.0 \text{ V}$ when SEL is shorted to VISO; $V_{ISO} = 5.4 \text{ V}$ when SEL is connected to VISO through a $100 \text{k}\Omega$ resistor; $V_{ISO} = 3.3 \text{ V}$ when SEL is shorted to GNDS; $V_{ISO} = 3.7 \text{V}$ when SEL is connected to GNDS through a $100 \text{k}\Omega$ resistor. Don't leave this pin open.
VISO	14	Power	Isolated supply voltage pin. Bypass VISO to GNDS with both $0.1\mu F$ and $10\mu F$ capacitors as close to the device as possible.

#### Note:

These pins do not have internal connection. We recommend to connect them to the corresponding ground plane to improve the PCB heat 1. dissipation.



# 7 Specifications

# 7.1 Absolute Maximum Ratings<sup>1, 2</sup>

	Parameters	Minimum value	Maximum value	Unit
V <sub>INP</sub>	Power supply voltage	-0.5	6.0	V
V <sub>ISO</sub>	Isolated supply voltage	-0.5	6.0	V
EN	EN input voltage	-0.5	V <sub>INP</sub> +0.3 <sup>3</sup>	V
SEL	SEL input voltage	-0.5	V <sub>ISO</sub> +0.3	V
T <sub>J</sub>	Junction temperature	-40	150	°C
T <sub>STG</sub>	Storage temperature range	-65	150	°C

#### Notes:

- 1. The stresses listed under "Absolute Maximum Ratings" are stress ratings only, not for functional operation condition. Exposure to absolute maximum rating conditions for extended periods may cause permanent damage to the device.
- 2. All voltage values are with respect to the local ground (GNDP or GNDS) and are peak voltage values.

Per JEDEC document JEP157, 250V CDM allows safe manufacturing of standard ESD control process.

3. Maximum voltage must not be exceed 6 V.

#### 7.2 ESD Ratings

		Value	Unit	
V <sub>ESD</sub> Electrostatic discharg	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>1</sup>	±3000	W	
V <sub>ESD</sub> Electrostatic discharg	Charged device model (CDM), per JEDEC Specification JESD22-C101, all pins <sup>2</sup>	±2000	V	
Notes:				
1. Per JEDEC document JEP155, 500V HBM allows safe manufacturing of standard ESD control process.				

# 7.3 Recommended Operating Conditions

	Parameters	linimum value	Typical value	Maximum value	Unit
V <sub>INP</sub>	Power supply voltage	4.5	5	5.5	V
V <sub>EN</sub>	EN input voltage	0		5.5	V
V <sub>ISO</sub>	Isolated supply voltage	0		5.7	V
$V_{SEL}$	SEL input voltage	0		5.7	V
T <sub>A</sub>	Ambient Temperature	-40		125	°C
T <sub>J</sub>	Junction temperature	-40		150	°C

#### 7.4 Thermal Information

Thermal Metric	CA-IS3105W	l lucia
Thermai Wetric	SOIC16-WB(W)	Unit
R <sub>0JA</sub> Junction-to-ambient thermal r	esistance 73.8	°C/W

# 7.5 **Power Ratings**

	Parameters	Test Conditions	Minimum value	Typical value	Maximum value	Unit
$P_D$	Power dissipation	$V_{INP}$ = 5.5V, $V_{ISO}$ = 5.4V, 130mA output current		1.27W	1.4	W



# 7.6 Insulation Specifications

	Parameters	Test Conditions	Specifications W	Unit
CLR	External clearance	Shortest terminal-to-terminal distance through air	8	mm
CPG	External creepage	Shortest terminal-to-terminal distance across the package surface	8	mm
DTI	Distance through the insulation	Minimum internal gap (internal clearance)	21	μm
CTI	Comparative tracking index	DIN EN 60112 (VDE 0303-11); IEC 60112	>400	V
	Material group	According to IEC 60664-1	I	
		Rated mains voltage ≤ 300 V <sub>RMS</sub>	I-IV	
	IEC 60664-1 over-voltage category	Rated mains voltage ≤ 400 V <sub>RMS</sub>	I-IV	
		Rated mains voltage ≤ 600 V <sub>RMS</sub>	1-111	
DIN V V	/DE V 0884-11:2017-01 <sup>1</sup>			
V <sub>IORM</sub>	Maximum repetitive peak isolation voltage	AC voltage (bipolar)	849	V <sub>PK</sub>
V <sub>IOWM</sub>	Maximum operating isolation voltage	AC voltage; time-dependent dielectric breakdown (TDDB) test	600	V <sub>RMS</sub>
10000		DC voltage	849	V <sub>DC</sub>
V <sub>IOTM</sub>	Maximum transient isolation voltage	$V_{TEST} = V_{IOTM}$ , t=60 s (qualification); $V_{TEST} = 1.2 \times V_{IOTM}$ , t=1 s (100% product test)	7070	V <sub>PK</sub>
V <sub>IOSM</sub>	Maximum surge isolation voltage <sup>2</sup>	Test method per IEC 60065, 1.2/50 $\mu$ s waveform, $V_{TEST} = 1.6 \times V_{IOSM}$ (production test)	6250	V <sub>PK</sub>
		Method a, after input/output safety tests subgroup 2/3, $V_{ini} = V_{IOTM}, t_{ini} = 60s; \\ V_{pd(m)} = 1.2 \times V_{IORM}, t_m = 10s \\ Method a, after environmental tests subgroup 1,$	≤5	
q <sub>pd</sub>	Apparent charge <sup>3</sup>	$\begin{aligned} &V_{ini} = V_{IOTM},  t_{ini} = 60s; \\ &V_{pd(m)} = 1.6 \times V_{IORM},  t_m = 10s \end{aligned}$	≤5	рC
		Method b1, at routine test (100% production test) and preconditioning (sample test) $V_{ini} = 1.2 \times V_{IOTM},  t_{ini} = 1s; \\ V_{pd(m)} = 1.875 \times V_{IORM},  t_m = 1s$	≤5	
C <sub>IO</sub>	Barrier capacitance, input to output <sup>4</sup>	$V_{10} = 0.4 \times \sin(2\pi ft), f = 1 \text{ MHz}$	3.5	pF
R <sub>IO</sub>	Isolation resistance , input to output <sup>4</sup>	$V_{IO} = 500 \text{ V}, T_A = 25^{\circ}\text{C}$ $V_{IO} = 500 \text{ V}, 100^{\circ}\text{C} \le T_A \le 125^{\circ}\text{C}$ $V_{IO} = 500 \text{ V} \text{ at } T_S = 150^{\circ}\text{C}$	>10 <sup>12</sup> >10 <sup>11</sup> >10 <sup>9</sup>	Ω
	Pollution degree		2	
UL 157		1	1	ı
V <sub>ISO</sub>	Maximum isolation voltage	$V_{TEST} = V_{ISO}$ , t = 60 s (certified) $V_{TEST} = 1.2 \times V_{ISO}$ , t = 1 s (100% production test)	5000	V <sub>RMS</sub>

#### Notes:

- 1. This coupler is suitable for "safe electrical insulation" only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.
- 2. Devices are immersed in oil during surge characterization.
- 3. The characterization charge is discharging charge (pd) caused by partial discharge.
- 4. Capacitance and resistance are measured with all pins on field-side and logic-side tied together.

# 7.7 Safety-Related Certifications

VDE (pending)	UL (pending)	CQC (pending)	TUV (pending)
Certified according to	Certified according to	Certified according to GB4943.1-	Certified according to EN61010-1:2010 (3rd
DIN V VDE V 0884-	UL 1577 Component	20111	Ed) and EN60950-1:2006/A2:2013
11:2017-01	Recognition Program		



# 7.8 Electrical Characteristics

Over operating temperature range  $T_A = -40$  to 125°C,  $V_{INP} = 4.5V$  to 5.5V, SEL connected to  $V_{ISO}$ ,  $C_{VINP} = C_{VISO} = 10\mu F$ , unless otherwise specified. All typical specs are at  $T_A = 25$ °C and  $V_{INP} = 5V$ .

Note		Parameters	Test Conditions	Minimum value	ТҮР	Maximum value	Unit		
No.	Power Sup	ply Input							
Figure - 28	I <sub>VINP_SD</sub>	V <sub>INP</sub> shutdown current	t EN = LOW, see Figure 7- 27 0.05						
Normal					8.4	20	mA		
EN   HiGH, SEL 100KQ to GNDS (3.7V output)	I <sub>VINP_O</sub>	•	EN = HIGH, SEL 100kΩ to VISO (5.4Voutput)		8.8	20	mA		
No.   DC current from VINP supply under short circuit on VISO   VISO short to GNDS   VISO short to GNDS short t		I <sub>OUT</sub> = 0% load	, , ,		7.3	20	mA		
					7.5	20	mA		
Threshold   Th	I <sub>VINP_SC</sub>	• • • •			42	100	mA		
threshold   th	V <sub>UVLO+</sub>	· · · · · · · · · · · · · · · · · · ·			2.6	3.0	V		
Nysteresis   Ny	V <sub>UVLO-</sub>			2.1	2.3		V		
Visto   Vis	V <sub>HYS(UVLO)</sub>	,			0.3	0.6	V		
VILO   Ninput Eakage current   Vinput Eakage curren	EN, SEL pir	ns							
Input leakage current   Vinin		EN Input threshold, logic HIGH		2			V		
Viso   Isolated DC-DC Converter   SEL connected to Viso (5V output), Iiso = 50mA   4.65   5.0   5.35   5EL 100KΩ to ViSO (5.4V output), Iiso = 50mA   5.02   5.4   5.78   5EL 100KΩ to SONDS (3.3V output), Iiso = 50mA   3.07   3.3   3.53   5EL 100KΩ to SONDS (3.3V output), Iiso = 50mA   3.44   3.7   3.96   20MHz bandwidth, SEL short to ViSO (5V output), Iiso = 50mA   3.44   3.7   3.96   20MHz bandwidth, SEL short to ViSO (5V output), Iiso = 50mA   3.44   3.7   3.96   20MHz bandwidth, SEL short to ViSO (5V output), Iiso = 50mA   3.44   3.7   3.96   20MHz bandwidth, SEL short to ViSO (5V output), Iiso = 50mA   3.44   3.7   3.96   3.96   3.90   3.	$V_{IL\_EN}$	EN Input threshold, logic LOW				0.8	V		
Viso   Isolated output voltage   SEL connected to Viso (5V output), Iso = 50mA   4.65   5.0   5.35   5.18   5.18   5.10   5.18   5.10   5.18   5.10   5.18   5.10   5.18   5.10   5.18   5.10   5.18   5.10   5.18   5.10   5.18   5.10   5.18   5.10   5.10   5.18   5.10   5.18   5.10   5.18   5.10   5.18   5.10   5.1	I <sub>EN</sub>	Input leakage current	$V_{INP} = 5V$ , $V_{EN} = 5V$		5	20	μΑ		
Viso   Isolated output voltage   SEL 100KΩ to ViSO (5.4V output), I <sub>Iso</sub> = 50mA   5.02   5.4   5.78   5.8	Isolated Do	C-DC Converter							
VISO   Isolated output voltage   SEL connected to GNDS (3.3V output),   Iso = 50mA   3.07   3.3   3.53			SEL connected to V <sub>ISO</sub> (5V output), I <sub>ISO</sub> = 50mA	4.65	5.0	5.35			
SEL connected to GNDS (3.3V output), I <sub>ISO</sub> = 50mA   3.07   3.3   3.53	Visa	Isolated output voltage	SEL 100K $\Omega$ to VISO (5.4V output), I <sub>ISO</sub> = 50mA	5.02	5.4	5.78	V		
VISO <sub>(RIP)</sub> output (pk-pk)         Voltage ripple on isolated supply output (pk-pk)         20MHz bandwidth, SEL short to VISO (5V output), I <sub>Iso</sub> = 100mA, see Figure 7- 9         65         100         mV           VISO <sub>(LINE)</sub> VISO <sub>(LINE)</sub> and the supplication         Line regulation         SEL short to VISO (5V output), I <sub>Iso</sub> = 50mA, V <sub>INP</sub> = 4.5V to 5.5 V, see Figure 7- 21         2         5         mV/V           VISO <sub>(LIOAD)</sub> VISO <sub>(LOAD)</sub> Load regulation         SEL short to VISO (5V output), I <sub>Iso</sub> = 50mA, V <sub>INP</sub> = 4.5V to 5.5 V, see Figure 7- 23         2         5         mV/V           SEL short to VISO (5V output), I <sub>Iso</sub> = 0 to 130mA, see Figure 7- 17         SEL short to GNDS (3.3V output), I <sub>Iso</sub> = 0 to 130mA, see Figure 7- 19         1%         2%         2%         5           EFF         Efficiency@maximum load current         I <sub>Iso</sub> = 130 mA, C <sub>LOAD</sub> = 0.1μF    10μF; V <sub>Iso</sub> =5V, see Figure 7- 25, Figure 7- 26         55%         55%         55%           CMTI         Common-mode transient immunity         Slew Rate of GNDP versus GNDS, V <sub>CM</sub> =1200V <sub>RMS</sub> ±100         ±150         kV/μs           V <sub>Iso</sub> ripple voltage (peak to peak)         10% to 90% load step with 10mA/us slew-rate; see Figure 7- 16, Figure 7- 14, Figure 7- 15, Figure 7- 15, Figure 7- 16         80         100         mV	VISO	isolated output voltage	SEL connected to GNDS (3.3V output), I <sub>ISO</sub> = 50mA	3.07	3.3	3.53	·		
VISO <sub>(RIP)</sub> output (pk-pk)         Voltage ripple on isolated supply output (pk-pk)         I <sub>ISO</sub> = 100mA, see Figure 7- 9         65         100         mV           VISO <sub>(LINE)</sub> VISO <sub>(LINE)</sub> Line regulation         SEL short to VISO (5V output), I <sub>ISO</sub> = 50mA, V <sub>INP</sub> = 4.5V to 5.5 V, see Figure 7- 21         2         5         mV/V           VISO <sub>(LOAD)</sub> VISO <sub>(LOAD)</sub> Load regulation         SEL short to VISO (5V output), I <sub>ISO</sub> = 50mA, V <sub>INP</sub> = 4.5V to 5.5V, see Figure 7- 21         2         5         mV/V           VISO <sub>(LOAD)</sub> VISO <sub>(LOAD)</sub> Load regulation         SEL short to VISO (5V output), I <sub>ISO</sub> = 0 to 130mA, see Figure 7- 19         1%         2%         5           EFF         Efficiency@maximum load current         I <sub>ISO</sub> = 130 mA, C <sub>LOAD</sub> = 0.1μF    10μF; V <sub>ISO</sub> =5V, see Figure 7- 25, Figure 7- 26         55%         55%         55%           CMTI         Common-mode transient immunity         Slew Rate of GNDP versus GNDS, V <sub>CM</sub> =1200V <sub>RMS</sub> ±100         ±150         kV/μs           V <sub>ISO</sub> ripple voltage (peak to peak)         10% to 90% load step with 10mA/us slew-rate; see Figure 7- 15, Figure 7- 16         80         100         mV				3.44	3.7	3.96			
Voltage ripple on isolated supply output (pk-pk)   Voltage ripple on isolated supply output (pk-pk)   Voltage ripple on isolated supply output (pk-pk)   20MHz bandwidth, SEL short to GNDS (3.3V output),   55   100			20MHz bandwidth, SEL short to VISO (5V output),		65	100			
20MHz bandwidth, SEL short to GNDS (3.3V output),   55   100     1   100   100   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100   100      1   100   100   100   100   100   100   100   100      1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100   100     1   100   100   100   100   100   100   100   100   100   100   100     1   100	VISO <sub>(RIP)</sub>		I <sub>ISO</sub> = 100mA, see Figure 7- 9		03 100 				
$VISO_{(IINE)} \begin{tabular}{l lllllllllllllllllllllllllllllllllll$			1		55	100	1110		
$ \begin{array}{c} V_{\text{INP}} = 4.5 \text{V to } 5.5 \text{ V, see Figure 7- } 21 \\ \hline SEL \text{ short to GNDS } (3.3 \text{V output}), I_{\text{ISO}} = 50 \text{mA}, \\ V_{\text{INP}} = 4.5 \text{V to } 5.5 \text{V, see Figure 7- } 23 \\ \hline \\ VISO_{(\text{LOAD})} \\ VISO_{(\text{LOAD})} \\ \hline \\ VISO_{(\text{LOAD})} \\ \hline \\ EFF \\ \hline \\ Efficiency@maximum load current \\ \hline \\ EMILION \\ \hline \\ EFF \\ \hline \\ EMILION \\ \hline \\ CMTI \\ \hline \\ Common-mode transient immunity \\ \hline \\ V_{\text{ISO}} = 130 \text{ mA}, C_{\text{LOAD}} = 0.1 \mu \text{F }   10 \mu \text{F; V}_{\text{ISO}} = 5 \text{V, see} \\ Figure 7- 26 \\ \hline \\ I_{\text{ISO}} = 130 \text{ mA}, C_{\text{LOAD}} = 0.1 \mu \text{F }   10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ Figure 7- 25, Figure 7- 26 \\ \hline \\ I_{\text{ISO}} = 130 \text{ mA}, C_{\text{LOAD}} = 0.1 \mu \text{F }   10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ Figure 7- 25, Figure 7- 26 \\ \hline \\ \hline \\ V_{\text{ISO}} = 130 \text{ mA}, C_{\text{LOAD}} = 0.1 \mu \text{F }   10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ Figure 7- 25, Figure 7- 26 \\ \hline \\ \hline \\ V_{\text{ISO}} = 130 \text{ mA}, C_{\text{LOAD}} = 0.1 \mu \text{F }   10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ Figure 7- 25, Figure 7- 26 \\ \hline \\ \hline \\ V_{\text{ISO}} = 130 \text{ mA}, C_{\text{LOAD}} = 0.1 \mu \text{F }   10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ Figure 7- 25, Figure 7- 26 \\ \hline \\ \hline \\ V_{\text{ISO}} = 130 \text{ mA}, C_{\text{IND}} = 0.1 \mu \text{F }   10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ Figure 7- 25, Figure 7- 26 \\ \hline \\ \hline \\ V_{\text{ISO}} = 130 \text{ mA}, C_{\text{IND}} = 0.1 \mu \text{F }   10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ Figure 7- 25, Figure 7- 26 \\ \hline \\ \hline \\ V_{\text{ISO}} = 130 \text{ mA}, C_{\text{IND}} = 0.1 \mu \text{F }   10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ Figure 7- 25, Figure 7- 26 \\ \hline \\ \hline \\ V_{\text{ISO}} = 130 \text{ mA}, C_{\text{IND}} = 0.1 \mu \text{F }   10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ Figure 7- 25, Figure 7- 26 \\ \hline \\ \hline \\ V_{\text{ISO}} = 130 \text{ mA}, C_{\text{IND}} = 130 \text{ mA}, C_{I$			- 11						
$\begin{tabular}{ l l l l l l l l l l l l l l l l l l l$			, , , , , , , , , , , , , , , , , , , ,		2	5			
$V_{\text{INP}} = 4.5 \text{V to } 5.5 \text{V, see Figure 7- } 23$ $V_{\text{ISO}_{(\text{LOAD})}}  \text{Load regulation}  \begin{array}{c} SEL \text{ short to VISO (5V output), } I_{\text{ISO}} = 0 \text{ to } 130 \text{mA, see} \\ Figure 7- 17 \\ SEL \text{ short to GNDS (3.3V output), } I_{\text{ISO}} = 0 \text{ to } 130 \text{mA, } \\ See \text{ Figure 7- 19} \\ I_{\text{ISO}} = 130 \text{ mA, } C_{\text{LOAD}} = 0.1 \mu \text{F} \mid\mid 10 \mu \text{F; V}_{\text{ISO}} = 5 \text{V, see} \\ Figure 7- 25, \text{ Figure 7- 26} \\ I_{\text{ISO}} = 130 \text{ mA, } C_{\text{LOAD}} = 0.1 \mu \text{F} \mid\mid 10 \mu \text{F; V}_{\text{ISO}} = 3.3 \text{V, see} \\ Figure 7- 25, \text{ Figure 7- 26} \\ CMTI  \text{Common-mode transient immunity}  \text{Slew Rate of GNDP versus GNDS, } V_{\text{CM}} = 1200 V_{\text{RMS}} \\ V_{\text{ISO}} = 100 \text{ to } 90\% \text{ load step with } 10 \text{mA/us slew-rate; see} \\ Figure 7- 13, \text{ Figure 7- 14, Figure 7- 15, Figure 7- 16} \\ \end{array}  \begin{array}{c} 2  Slew Policy for the property of the$	VISO <sub>(LINE)</sub>	Line regulation					mV/V		
$VISO_{(LOAD)}  Load \ regulation \\ \\ EFF  Efficiency@maximum \ load \ current \\ \\ EFF  Efficiency@maximum \ load \ current \\ \\ VISO \ ripple \ voltage \ (peak \ to peak) \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$					2	5			
$VISO_{(LOAD)}  Load \ regulation \qquad \begin{array}{c} Figure 7-17 \\ \hline SEL \ short \ to \ GNDS \ (3.3V \ output), \ I_{ISO} = 0 \ to \ 130 mA, \\ see \ Figure 7-19 \\ \hline \\ I_{ISO} = 130 \ mA, \ C_{LOAD} = 0.1 \mu F \mid \mid 10 \mu F; \ V_{ISO} = 5V, \ see \\ Figure 7-25, \ Figure 7-26 \\ \hline \\ CMTI  Common-mode \ transient \ immunity \\ \hline \\ V_{ISO} \ ripple \ voltage \ (peak \ to \ peak) \\ \hline \end{array}$			·		1%	2%			
$ \begin{array}{c} \text{VISO}_{\text{(LOAD)}} & \text{Load regulation} \\ & \text{SEL short to GNDS (3.3V output), } I_{\text{ISO}} = 0 \text{ to } 130\text{mA}, \\ & \text{see Figure7- 19} \\ \\ & I_{\text{ISO}} = 130 \text{ mA, } C_{\text{LOAD}} = 0.1 \mu \text{F} \mid \mid 10 \mu \text{F; } V_{\text{ISO}} = 5 \text{V, see} \\ & \text{Figure7- 25, Figure7- 26} \\ \\ & I_{\text{ISO}} = 130\text{mA, } C_{\text{LOAD}} = 0.1 \mu \text{F} \mid \mid 10 \mu \text{F; } V_{\text{ISO}} = 3.3 \text{V, see} \\ & \text{Figure7- 25, Figure7- 26} \\ \\ & \text{CMTI} & \text{Common-mode transient immunity} \\ & \text{Slew Rate of GNDP versus GNDS, } V_{\text{CM}} = 1200 V_{\text{RMS}} \\ & \text{$\pm 100$} & \text{$\pm 150$} \\ & \text{$\pm 100$} & \text{$\pm 150$} \\ & \text{$V/\mu \text{SO}} \\ & \text{Figure7- 13, Figure7- 14, Figure7- 15, Figure7- 16} \\ \end{array} $					_,-				
$ EFF  Efficiency@maximum load current \\ \hline EFF  Efficiency@maximum load current \\ \hline I_{ISO} = 130  mA,  C_{LOAD} = 0.1 \mu F \mid \mid 10 \mu F;  V_{ISO} = 5V,  see \\ \hline Figure7- 25,  Figure7- 26 \\ \hline I_{ISO} = 130  mA,  C_{LOAD} = 0.1 \mu F \mid \mid 10 \mu F;  V_{ISO} = 3.3V,  see \\ \hline Figure7- 25,  Figure7- 26 \\ \hline CMTI  Common-mode transient immunity \\ \hline V_{ISO}  ripple  voltage  (peak  to  peak) \\ \hline \begin{tabular}{ll} I_{ISO} = 130  mA,  C_{LOAD} = 0.1 \mu F \mid \mid 10 \mu F;  V_{ISO} = 3.3V,  see \\ \hline Figure7- 26 \\ \hline \begin{tabular}{ll} 48\% \\ \hline \begin{tabular}{ll} V_{ISO} = 130  mA,  C_{LOAD} = 0.1 \mu F \mid \mid 10 \mu F;  V_{ISO} = 3.3V,  see \\ \hline \begin{tabular}{ll} 48\% \\$	VISO <sub>(LOAD)</sub>	Load regulation			1%	2%			
			see Figure7- 19						
$I_{ISO} = 130$ mA, $C_{LOAD} = 0.1$ μF     $10$ μF; $V_{ISO} = 3.3$ V, see Figure 7- 25, Figure 7- 26  CMTI Common-mode transient immunity Slew Rate of GNDP versus GNDS, $V_{CM} = 1200$ V <sub>RMS</sub> $\pm 100$ $\pm 150$ kV/μs $V_{ISO}$ ripple voltage (peak to peak) $10\%$ to 90% load step with 10mA/us slew-rate; see Figure 7- 13, Figure 7- 14, Figure 7- 15, Figure 7- 16	CCC	Efficiency@maximum load current			55%				
V <sub>Iso</sub> ripple voltage (peak to peak)  10% to 90% load step with 10mA/us slew-rate; see Figure7- 13, Figure7- 14, Figure7- 15, Figure7- 16  80  100  mV	CFF	Emclency@maximum load current			48%				
V <sub>ISO</sub> ripple voltage (peak to peak)  Figure 7- 14, Figure 7- 15, Figure 7- 16	CMTI	Common-mode transient immunity	Slew Rate of GNDP versus GNDS, V <sub>CM</sub> =1200V <sub>RMS</sub>	±100	±150		kV/μs		
Transient Output Power (overload) $V_{INP} = 5V$ , $V_{ISO} = 5.4V$ 1 W	V <sub>ISO</sub> ripple	voltage (peak to peak)	•		100	mV			
	Transient C	Output Power (overload)	V <sub>INP</sub> = 5V, V <sub>ISO</sub> = 5.4V	1			W		

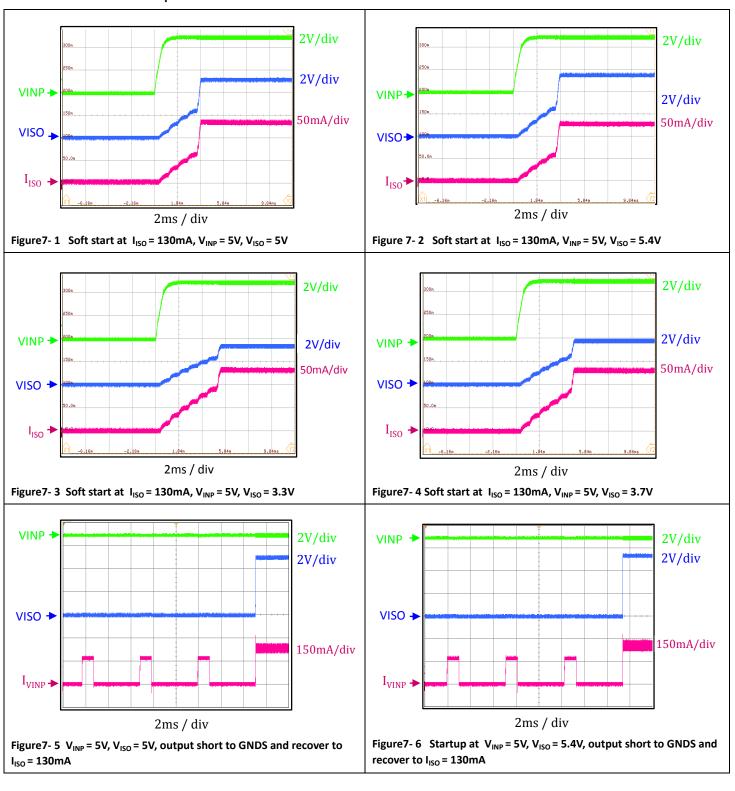
# 7.9 **MSL**

Parameters	Standard	Level		
MSL	IPC/JEDEC J-STD-020D.1	MSL 3		



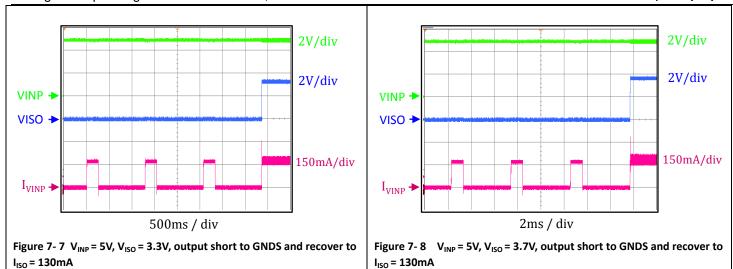
# 7.10 **Typical Operating Characteristics**

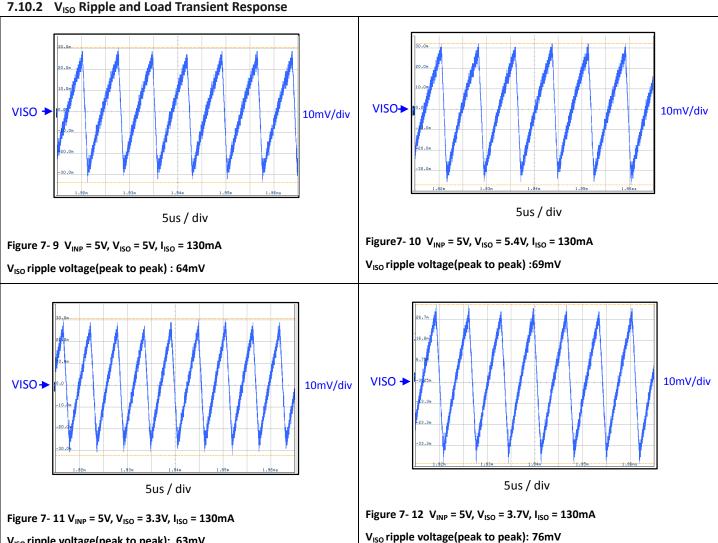
# 7.10.1 Soft-Start and Output Short-Circuit Protection





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V<sub>ISO</sub> ripple voltage(peak to peak): 63mV



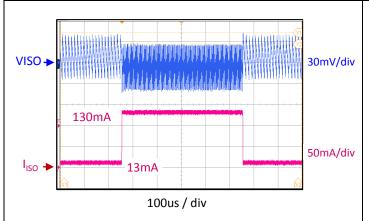


Figure 7- 13  $V_{ISO}$  Load transient response  $V_{INP}$  = 5V,  $V_{ISO}$  = 5V, Load step: 13mA to 130mA

V<sub>ISO</sub> ripple voltage(peak to peak): 16mV

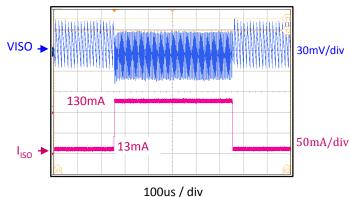


Figure 7- 14  $V_{ISO}$  Load transient response  $V_{INP}$  = 5V,  $V_{ISO}$  = 5.4V, Load step: 13mA to 130mA

V<sub>ISO</sub> ripple voltage(peak to peak): 17mV

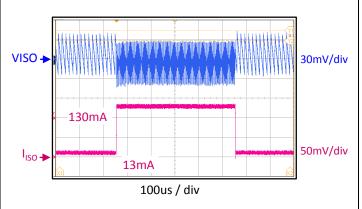


Figure 7- 15  $V_{ISO}$  Load transient response:  $V_{INP}$  = 5V,  $V_{ISO}$  = 3.3V, Load step: 13mA to 130mA

V<sub>ISO</sub> ripple voltage(peak to peak): 15mV

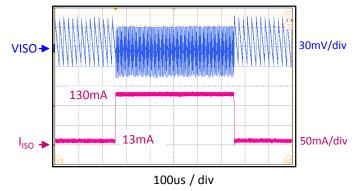


Figure 7- 16  $V_{ISO}$  Load transient response:  $V_{INP}$  = 5V,  $V_{ISO}$  = 3.7V, Load step: 13mA to 130mA

V<sub>ISO</sub> ripple voltage(peak to peak): 16mV

# 7.10.3 Isolated Supply Voltage Typical Characteristics

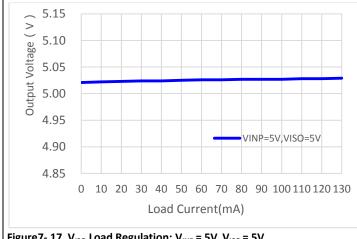


Figure 7- 17  $V_{ISO}$  Load Regulation;  $V_{INP}$  = 5V,  $V_{ISO}$  = 5V

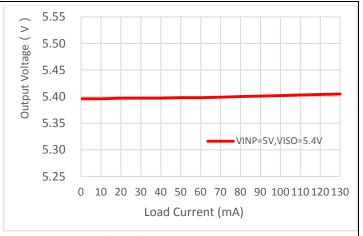
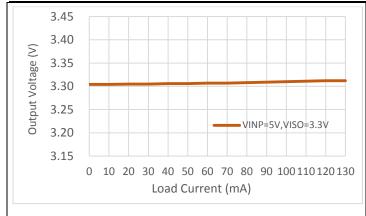


Figure 7- 18  $V_{ISO}$  Load Regulation;  $V_{INP} = 5V$ ,  $V_{ISO} = 5.4V$ 



# Shanghai Chipanalog Microelectronics Co., Ltd.



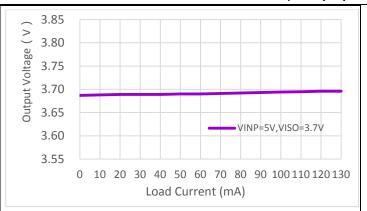
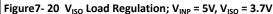
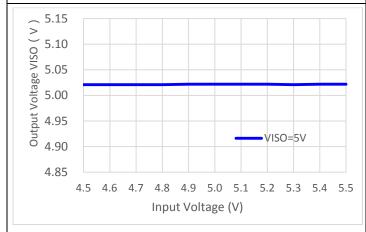


Figure 7- 19  $V_{ISO}$  Load Regulation;  $V_{INP}$  = 5V,  $V_{ISO}$  = 3.3V





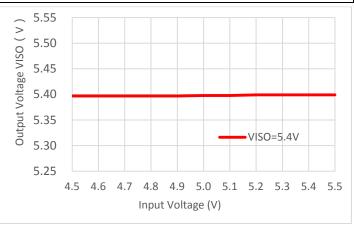
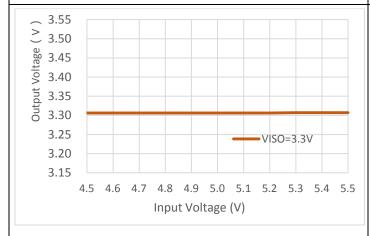


Figure 7- 21  $V_{ISO}$  Line Regulation;  $V_{INP}$  = 4.5V to 5V,  $V_{ISO}$  = 5V

Figure 7-22  $V_{ISO}$  Line Regulation;  $V_{INP} = 4.5V$  to 5V,  $V_{ISO} = 5.4V$ 



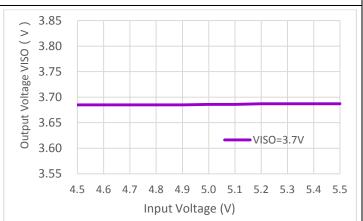


Figure 7-23  $V_{ISO}$  Line Regulation;  $V_{INP} = 4.5V$  to 5V,  $V_{ISO} = 3.3V$ 

Figure 7- 24  $V_{ISO}$  Line Regulation;  $V_{INP}$  = 4.5V to 5V,  $V_{ISO}$  = 3.7V

#### 7.10.4 Power Supply Efficiency vs. Load Current

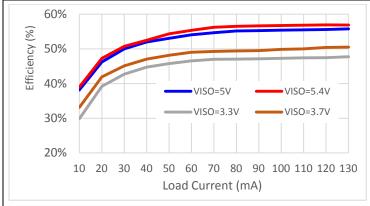


Figure 7- 25 Power Supply Efficiency vs. Load Current

 $V_{INP} = 5V$ ,  $V_{ISO} = 5V$ ;  $V_{INP} = 5V$ ,  $V_{ISO} = 5.4V$ ;  $V_{INP} = 5V$ ,  $V_{ISO} = 3.3V$ ;  $V_{INP} = 5V$ ,  $V_{ISO} = 3.7V$ 

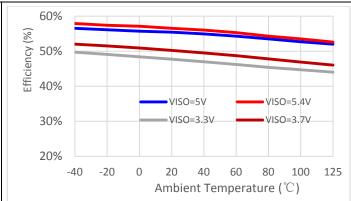


Figure 7-26 Power Supply Efficiency vs. Temperature

 $V_{INP} = 5V$ ,  $V_{ISO} = 5V$ ;  $V_{INP} = 5V$ ,  $V_{ISO} = 5.4V$ ;  $V_{INP} = 5V$ ,  $V_{ISO} = 3.3V$ ;  $V_{INP} = 5V$ ,  $V_{ISO} = 3.7V$ 

#### 7.10.5 Quiescent Current and Shutdown Current

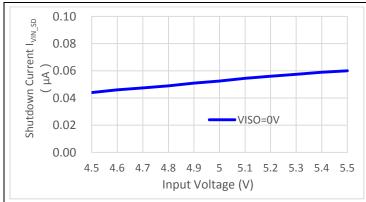


Figure 7-27 Shutdown Current vs. Input voltage;

 $V_{INP}$  = 4.5V to 5.5V, EN connected to GNDP

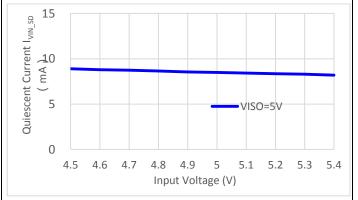
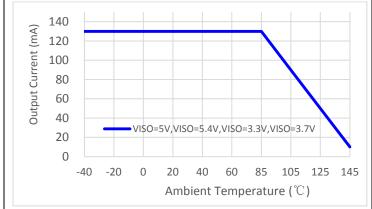


Figure 7-28 Quiescent Current vs. Input Voltage  $V_{INP}$  = 4.5V to 5.5V,  $V_{ISO}$  = 5V, EN connected to VINP

# 7.10.6 Maximum Output Current vs. Temperature





# 8 Detailed Description

#### 8.1 Overview

The CA-IS3105W is a complete isolated DC-DC converter designed to provide isolated power with up to 650mW output power across a 5kV<sub>RMS</sub> isolation barrier. The device operates over 4.5V to 5.5V input and uses a proprietary control mechanisms. The input supply V<sub>INP</sub> is provided to the primary power controller that switches the power stage connected to the integrated transformer. Power is transferred to the secondary side and regulated to a fixed output voltage set by the SEL pin. The soft-start feature allows to reduce input inrush current and avoid output overshoot. The device also incorporates an output enable (EN) control and undervoltage lockout function that allows the user to turn on the part at the desired input-voltage level. Figure 8-1 shows the CA-IS3105's functional block diagrams. Connect the EN pin to the VINP pin or force this pin high to turn on the DC-DC converter. Force this pin low to disable the device and enter low-current shutdown mode. This device offers a ready-made, reliable, easy-to-use solution and allows users save PCB space and reduce design time for the popular 5V, 3.3V voltage rails.

The device is provided with a robust overcurrent protection scheme that protects the device under overload and output short-circuit conditions. A cycle-by-cycle peak current limit turns off the switching operation and triggers a hiccup mode. Once the hiccup timeout period expires, soft-start is attempted again. Hiccup mode operation ensures low power dissipation under output short-circuit conditions.

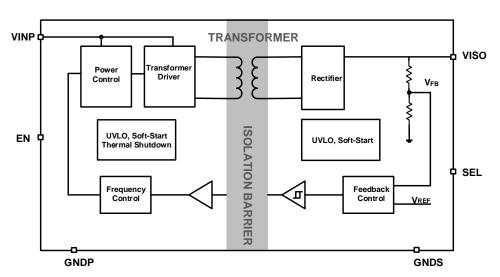


Figure 8-1 Functional Block Diagrams

# 8.2 Output Voltage Selection

At startup, the CA-IS3105W monitors the state of pin SEL after applying  $V_{INP}$  supply voltage above the UVLO rising threshold or enabling via the EN pin, to detect the desired regulation voltage level for the  $V_{ISO}$  output. After this initial monitoring, the SEL pin no longer affects the  $V_{ISO}$  output level. In order to change the output level, either the EN pin must be toggled or the  $V_{INP}$  power supply must be cycled off and back on. See Table. 8-1 for the output voltage selection.

ΕN SEL VISO High Sorted to VISO 5V High  $100k\Omega$  to VISO 5.4V Shorted to GNDS 3.3V High 100KΩ to GNDS High 3.7V OPEN Unsupported High Low Χ ٥v

Table. 8-1 V<sub>ISO</sub> Output Voltage Selection



#### 8.3 Protection Functions

#### 8.3.1 UVLO and Soft-Start

The CA-IS3105W has an undervoltage lockout (UVLO) on the  $V_{INP}$  power supply. Upon power-up, while the  $V_{INP}$  voltage is below the threshold voltage  $V_{UVLO+}(2.6V, typ.)$  the primary side transformer driver is disabled, and  $V_{ISO}$  output is off. The output powers up once the threshold is met. This allows the user to turn on the part at stable input-voltage level.

For many applications, it is necessary to minimize the inrush current at start-up. The CA-IS3105W built-in soft-start circuit significantly reduces the start-up current spike and output voltage overshoot. Once input power supply is applied at VINP pin, the internal soft-start circuit will control the power delivered to the output gradually increase, allowing for a graceful turn-on ramp.

#### 8.3.2 Overcurrent Protection

The CA-IS3105W is provided with an over-current protection scheme that protects the device under overload and output short-circuit conditions. A cycle-by-cycle peak current limit turns off the switching operation and triggers a hiccup mode whenever the switch current exceeds the internal current limit. Once the hiccup timeout period expires, soft-start is attempted again. The hiccup condition is cleared when the over-current is removed.

#### 8.3.3 Thermal Shutdown

Thermal-shutdown protection limits total power dissipation in the device. When the junction temperature of the device exceeds  $T_{SD}$ , an on-chip thermal sensor shuts down the device, allowing the device to cool. The thermal sensor turns the device on again after the junction temperature cools and junction temperature drops to normal operation temperature range of the device.

#### 9 Applications Information

#### 9.1 Typical Application Circuit

The CA-IS3105W is high-integration isolated power supply solution. Included in the package are the switching controller, power switches, transformer, and all support components. Only output and input bypass capacitors are needed to finish the design. For the applications with LDO post regulator, it may need a single  $100k\Omega$  external resistor to set the output level to 3.7V or 5.4V, see Figure 9-1 typical application circuit.

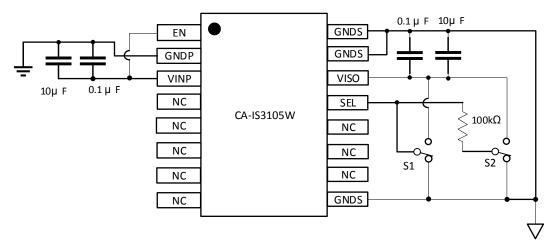


Figure 9-1 CA-IS3105W Typical Application Circuit



#### 9.2 Input and Output Capacitors

The input capacitors (between VINP and GNDP) are required to reduce the peak current drawn from input power source and reduce the switching noise, increase efficiency. For the input capacitors, choose the ceramic capacitor because they have the lowest equivalent series resistance (ESR), smallest size, and lowest cost. For most applications, we recommend to use at least  $0.1\mu F$  and  $10\mu F$  ceramic capacitors with X5R or X7R temperature characteristic. When operating at a VINP voltage close to the UVLO threshold, more input capacitance may be required to keep the input voltage ripple from tripping the UVLO protection.

The output capacitors between VISO and GNDS are required as well to keep the output voltage ripple small and to ensure loop stability. These bypass capacitors must have low impedance at the switching frequency. Ceramic capacitors are recommended due to their small size and low ESR. Make sure the capacitor does not degrade its capacitance significantly over temperature and DC bias. It is recommended to have at least 10µF of effective capacitance at output.

#### 9.3 PCB Layout Guidelines

High switching frequencies and large peak currents make PCB layout a very important part of the DC-DC converter design. Good PCB design minimizes excessive electromagnetic interference (EMI) and voltage gradients in the ground plane to avoid instability and regulation errors. Even with the high level of integration, like CA-IS3105W, users may fail to achieve specified operation with a haphazard or poor layout. So careful PCB layout is critical to achieve clean and stable operation, and ensure that the grounding and heat sinking are acceptable.

The input capacitors should be placed as close as possible to the CA-IS3105W's VINP and GNDP pins. Place the output capacitors as close as possible to VISO and GNDS pins, see Figure 9-2 recommended components placement for the PCB layout. Connect all of the ground (GNDP, GNDS) connections to as large a copper pour or plane area as possible for best heat-sinking. To ensure isolation performance between the primary and secondary side, avoid placing any PCB traces or copper below the CA-IS3105W device on the outer copper layers.

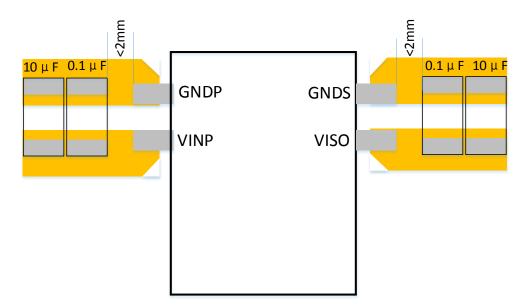
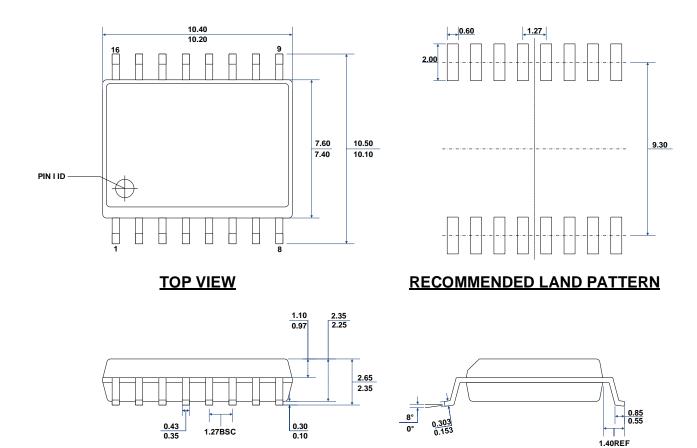


Figure 9-2 Recommended Bypass Capacitors Placement



# 10 Package Information

The following figure illustrates the size drawing and recommended pad size of SOIC16-WB wide-body package for the CA-IS3105W isolated DC-DC converter. All dimensions are in millimeters.



**LEFT-SIDE VIEW** 



# 11 Soldering Temperature (reflow) Profile

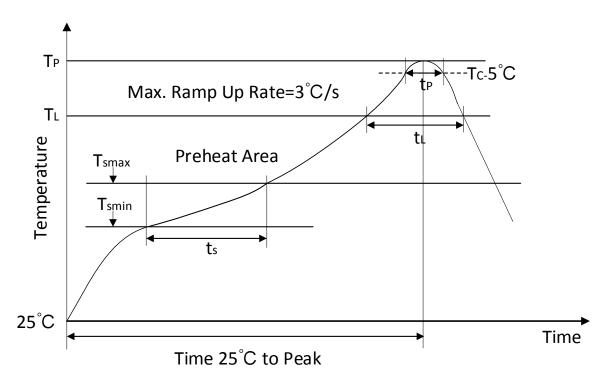


Figure 11-1 Soldering Temperature (reflow) Profile

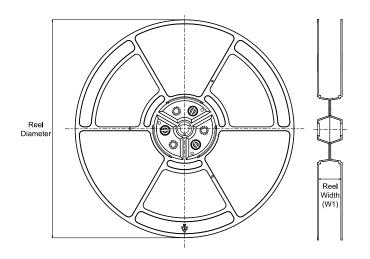
**Table 11-1 Soldering Temperature Parameter** 

Profile Feature	Pb-Free Assembly
Average ramp-up rate(217 °C to Peak)	3℃/second max
Time of Preheat temp(from 150 $^{\circ}\mathrm{C}$ to 200 $^{\circ}\mathrm{C}$	60-120 second
Time to be maintained above 217 $^{\circ}{\mathbb{C}}$	60-150 second
Peak temperature	260 +5/-0 °C
Time within 5 °C of actual peak temp	30 second
Ramp-down rate	6 °C/second max.
Time from 25 °C to peak temp	8 minutes max

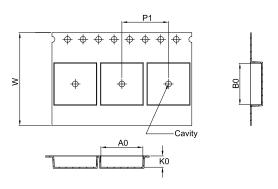


# 12 Tape and Reel Information

# **REEL DIMENSIONS**

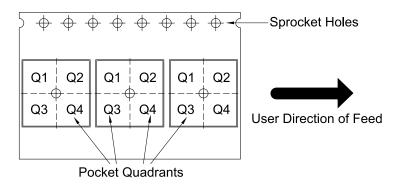


#### **TAPE DIMENSIONS**



A0	Dimension designed to accommodate the component width					
В0	Dimension designed to accommodate the component length					
K0	Dimension designed to accommodate the component					
	thickness					
W	Overall width of the carrier tape					
P1	Pitch between successive cavity centers					

# QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



# \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	KO (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CA-IS3105W	SOIC	W	16	1000	330	16.4	10.8	10.7	2.9	12.0	24.0	Q1



# 13 Important statement

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